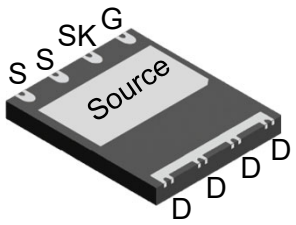
Prisemi®

PGC8N70R240BL

700V GaN Power Transistor

Description

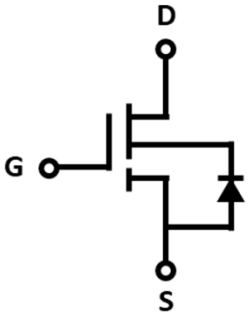
Product Summary		
V_{DS}(V)	$R_{DS(on)}$(mΩ)(Typ)	I_D(A)
700	240	6.5



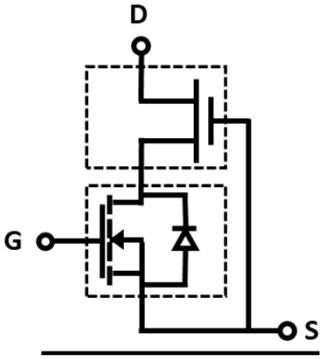
DFN5×6 (Bottom View)

Feature

- Easy to use, compatible with standard gate drivers
- Excellent Q_G x $R_{DS(on)}$ figure of merit (FOM)
- Low Q_{RR}, no free-wheeling diode required
- Low switching loss
- RoHS compliant and Halogen-free



Schematic Symbol



Cascode
Device Structure

Applications

- High efficiency power supplies
- Telecom and datacom
- Automotive
- Servo motors

Absolute maximum rating@25℃

Parameter		Symbol	Rating	Unit
Drain-Source Voltage		V_{DS}	700	V
Gate-Source Voltage		V_{GS}	±20	V
Transient Drain-Source Voltage[1]		V_{TDS}	800	V
Continuous Drain Current	T_C=25℃	I_D	6.5	A
	T_C=100℃		4	
Pulsed Drain Current (Pulse Width: 100μs)	T_C=25℃	I_{DM}	19	A
	T_C=150℃		15	
Power Dissipation		P_D	19	W
Soldering Peak Temperature		T_{CSOLD}	260	℃
Operating Junction and Storage Temperature		T_J, T_{STG}	-55 to 150	℃

Thermal Resistance

Parameter	Symbol	Min	Typ	Max	Unit
Thermal Resistance, Junction-to-Case	$R_{θJC}$	-	6.5	-	℃/W
Thermal Resistance, Junction-to-Ambient[2]	$R_{θJA}$	-	50	-	℃/W

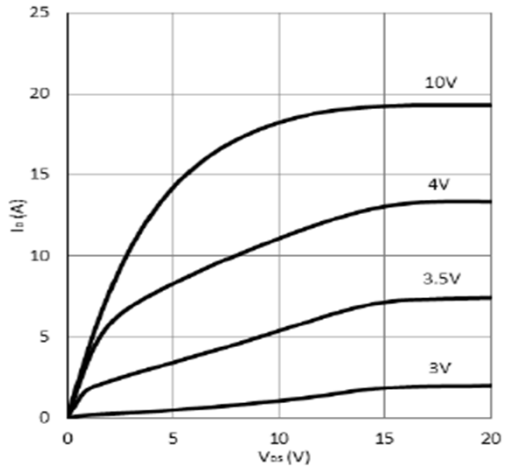
Electrical characteristics per line@25℃ (unless otherwise specified)

Parameter	Symbol	Conditions		Min.	Typ.	Max.	Units
Statistic Characteristics							
Maximum Drain-Source Voltage	V_{DS-Max}	V_{GS} = 0V		700	-	-	V
Drain-Source Breakdown Voltage	BV_{DSS}	V_{GS} = 0V,I_D = 250μA		-	1000	-	V
Zero Gate Voltage Drain Current	I_{DSS}	V_{DS}=700V, V_{GS}=0V	T_J=25℃	-	8	20	μA
			T_J=150℃	-	50	-	
Gate-Body Leakage Current	I_{GSS}	V_{GS} = ±20V,V_{DS} = 0V		-	-	±150	nA
Gate Threshold Voltage	$V_{GS(th)}$	V_{DS} = V_{GS},I_D = 500μA		1.1	1.8	2.5	V
Drain-Source On-State Resistance[3]	$R_{DS(ON)}$	V_{GS}=8V, I_D=4A	T_J=25℃	-	240	300	mΩ
			T_J=150℃	-	480	-	
Dynamic Characteristics							
Input Capacitance	C_{lss}	V_{DS} = 400V,V_{GS} = 0V, f = 1MHz		-	289	-	pF
Output Capacitance	C_{oss}			-	16	-	
Reverse Transfer Capacitance	C_{rss}			-	0.6	-	
Effective Output Capacitance, Energy Related	$C_{o(er)}$	V_{GS} = 0V, V_{DS} = 0-400V		-	24	-	pF
Effective Output Capacitance, Time Related	$C_{o(tr)}$			-	66	-	
Output Charge	Q_{oss}			-	27	-	nC
Turn-on Delay Time	$t_{d(on)}$	V_{DS} = 400V,I_D = 4A, V_{GS} =0-8V,R_G=47Ω		-	28	-	ns
Turn-on Rise Time	t_r			-	14	-	
Turn-Off Delay Time	$t_{d(off)}$			-	108	-	
Turn-Off Fall Time	t_f			-	8	-	
Total Gate Charge	Q_g	V_{DS} = 400V,I_D = 4A, V_{GS} =0-8V		-	5.6	-	nC
Gate-Source Charge	Q_{gs}			-	1.5	-	
Gate-Drain Charge	Q_{gd}			-	2	-	
Reverse Diode Characteristics							
Diode Forward Voltage	V_{SD}	V_{GS}=0V, I_S=2A		-	1.3	-	V
		V_{GS}=0V, I_S=4A	T_J=25℃	-	1.8	-	
			T_J=150℃	-	2.7	-	
Reverse Recovery Time	t_{rr}	V_{GS}=0V, I_S=4A, V_{DD}=400V, di/dt=1000A/μs		-	16	-	ns
Reverse Recovery Charge	Q_{rr}			-	27	-	μC

Notes:
1. Off-state spike duty cycle < 0.01, spike duration < 2μs
2. Device on one layer epoxy PCB for drain connection (vertical and without air stream cooling, with 6cm²copper area and 70μm thickness)
3. Dynamic on-resistance; see Figure 19 and 20 for test circuit and configurations

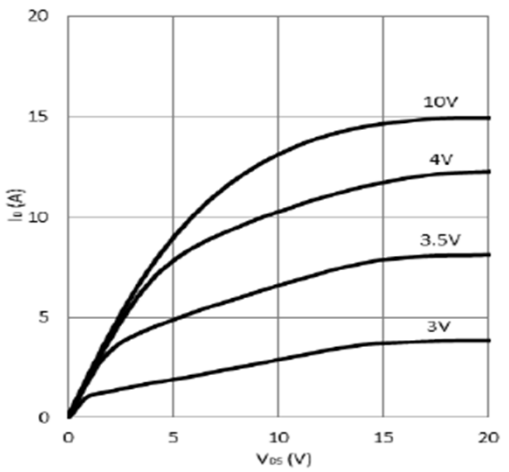
Typical Characteristics

Figure 1. Typical Output Characteristics T_J=25℃



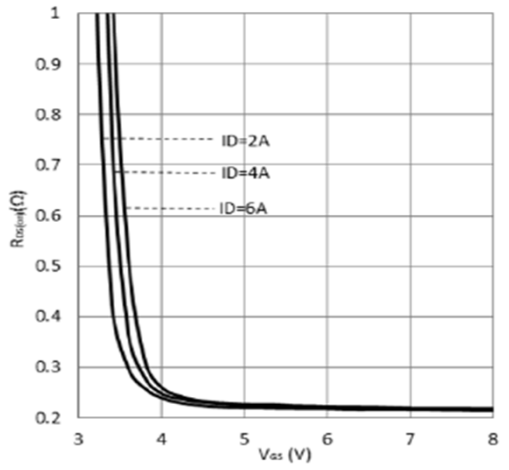
Parameter: V_{GS}

Figure 2. Typical Output Characteristics T_J=150℃



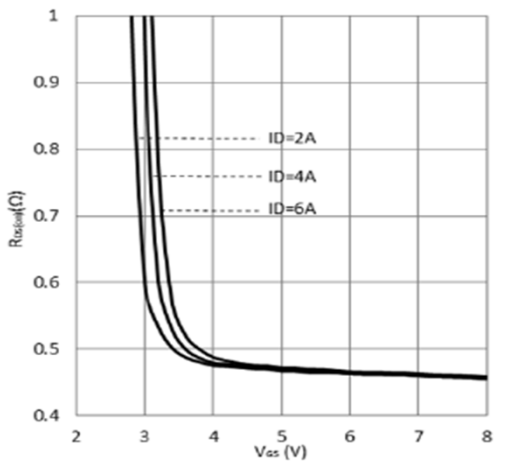
Parameter: V_{GS}

Figure 3.Typical Drain to Source On-resistance T_J= 25°C



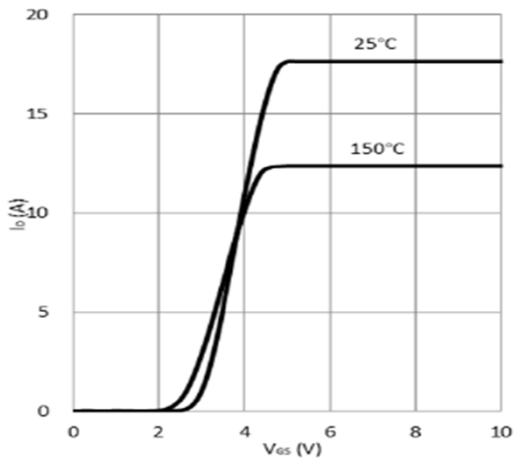
Parameter: I_D

Figure 4. Typical Drain to Source On-resistance T_J= 150°C



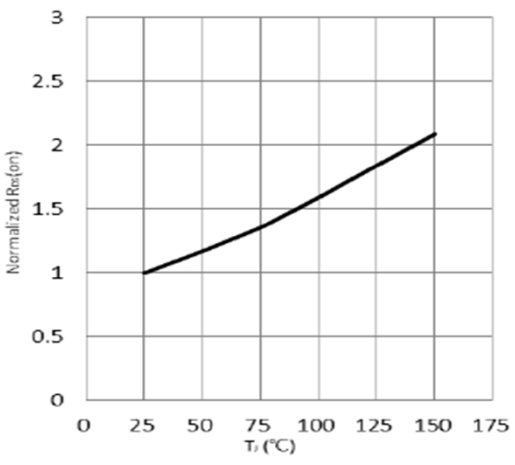
Parameter: I_D

Figure 5. Typical Transfer Characteristics



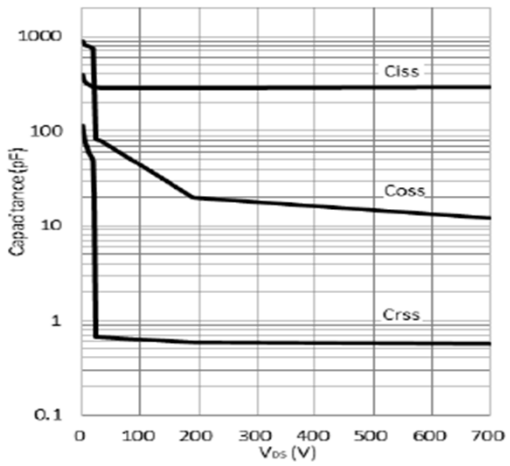
V_{DS}=10V, Parameter: T_J

Figure 6. Normalized On-resistance



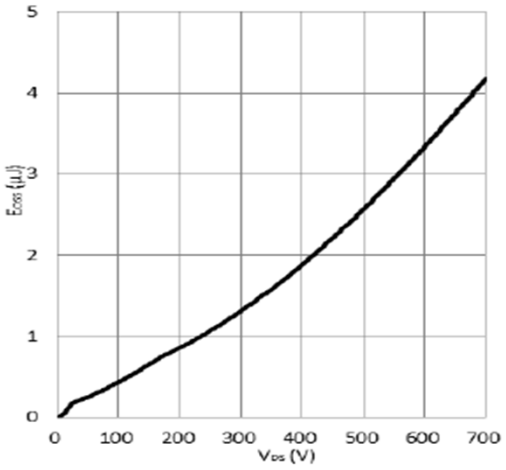
I_D=4A, V_{GS}=8V

Figure 7. Typical Capacitance



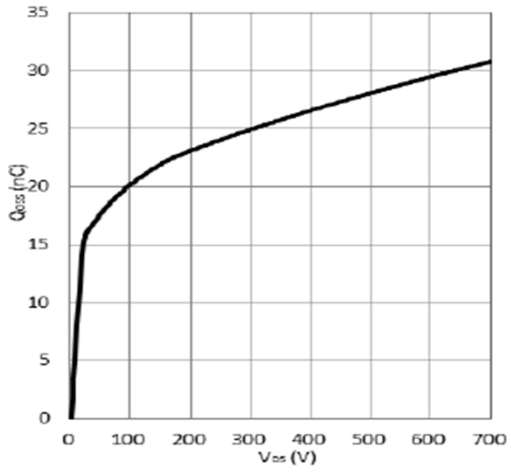
V_{GS}=0V, f=1MHz

Figure 8. Typical Coss Stored Energy



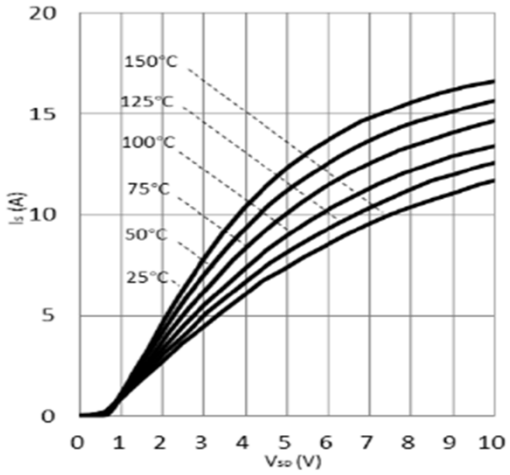
V_{GS}=0V, f=1MHz

Figure 9. Typical Qoss



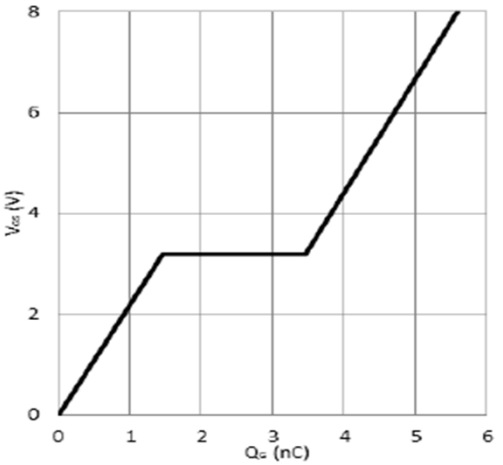
V_{GS}=0V, f=1MHz

Figure 10. Forward Characteristic of Rev. Diode



$I_S=f(V_{SD})$, Parameter T_J

Figure 11. Typical Gate Charge



I_{DS}=4A, V_{DS}=400V

Figure 12. Power Dissipation

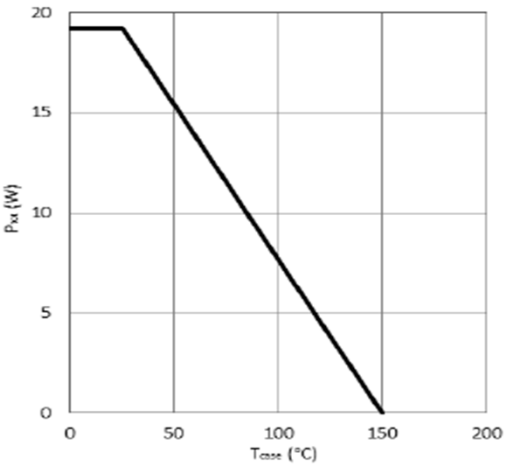


Figure 13. Current Derating

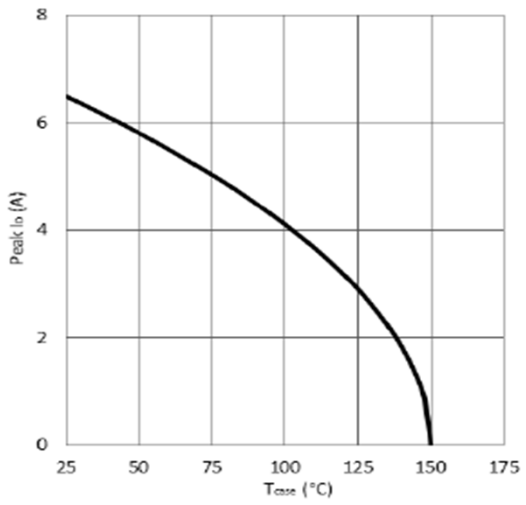


Figure 14. Transient Thermal Resistance

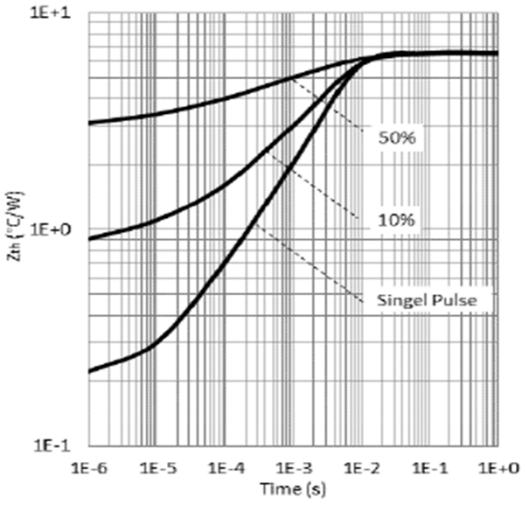
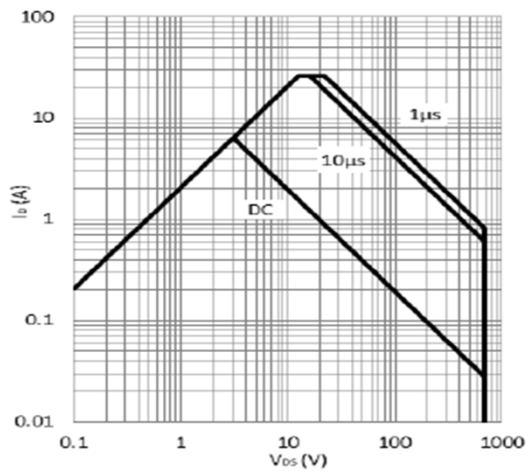
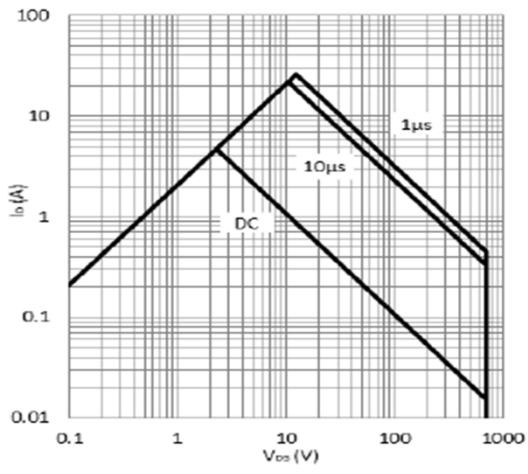


Figure 15. Safe Operating Area T_c=25℃



calculated based on thermal limit

Figure 16. Safe Operating Area T_c=80℃



calculated based on thermal limit

Test Circuits and Waveforms

Figure 17. Switching Time Test Circuit

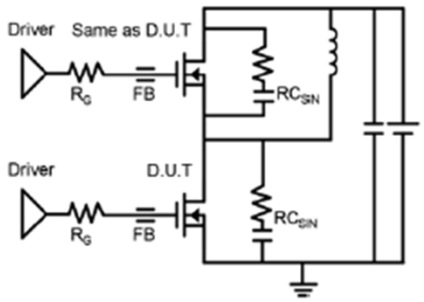


Figure 18. Switching Time Waveform

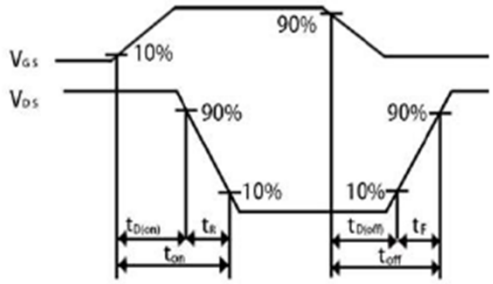


Figure 19. Dynamic $R_{DS(on)}$ Test Circuit

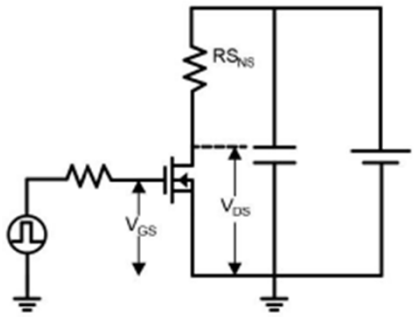


Figure 20. Dynamic $R_{DS(on)}$ Waveform

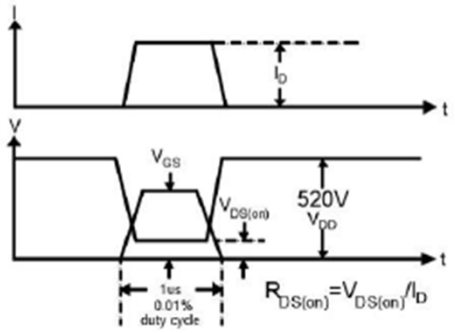


Figure 21. Diode Characteristic Test Circuits

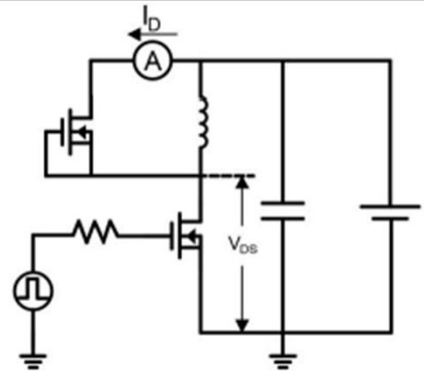
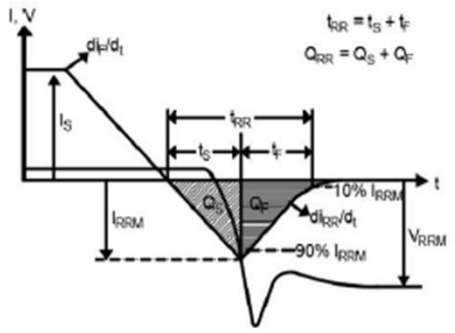
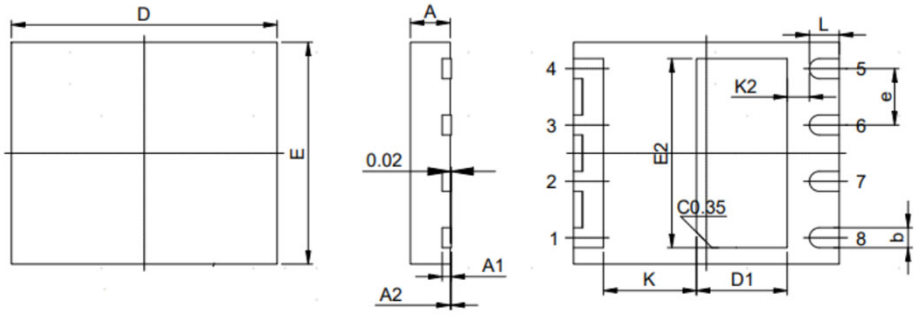


Figure 22. Diode Recovery Waveform



Product Dimension (DFN5×6)



TOP VIEW SIDE VIEW(RIGHT) BOTTOM VIEW

SIDE VIEW(FRONT)

SYMBOL	Millimeter		
	Min	Nom	Max
A	0.80	0.90	1.00
A1	0.203REF.		
A2	0	0.02	0.05
b	0.40	0.45	0.50
D	5.90	6.00	6.10
D1	1.95	2.05	2.15
e	1.27BSC		
E	4.90	5.00	5.10
E2	4.16	4.26	4.36
L	0.625	0.675	0.725
K	2.10REF.		
K2	0.50REF.		

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